

| | U | 1 | Document ID | Title |
|---|---|---|-------------------|---|
| 1 | | | US 20040065903 A1 | Integrated circuit with MOSFETS having bi-layer metal gate electordes and method of making same |
| 2 | X | | US 6879009 B2 | Integrated circuit with MOSFETS having bi-layer metal gate electrodes |
| 3 | X | | US 6696333 B1 | Method of making integrated circuit with MOSFETs having bi-layer metal gate electrodes |
| 4 | X | | US 6479403 B1 | Method to pattern polysilicon gates with high-k material gate dielectric |
| 5 | X | | US 6380063 B1 | Raised wall isolation device with spacer isolated contacts and the method of so forming |
| 6 | X | | US 6218276 B1 | Silicide encapsulation of polysilicon gate and interconnect |

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| 7 | X | | US 6100173 A | Forming a self-aligned silicide gate conductor to a greater thickness than junction silicide structures using a dual-salicidation process |
| 8 | X | | US 6638829 B | Manufacture of semiconductor structure by forming polysilicon alignment structure, growing epitaxial layer, removing polysilicon alignment structure, planarizing and etching oxide layer, forming silicide layer, and forming gate electrode |
| 9 | X | | US 6218276 B | Formation of semiconductor device by forming refractory metal silicide layer on vertical sidewall surfaces of gate electrode, on top surface of gate electrode, and on source and drain regions |

| | Type | L # | Hits | Search Text | DBs |
|---|------|-----|------|--|--|
| 1 | BRS | L1 | 483 | ((spacer\$1) near35 (gate)) near25 (remov\$3)) near25 (silicide) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 2 | BRS | L2 | 335 | ((sidewall\$1) near35 (gate)) near25 (remov\$3)) near25 (silicide) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 3 | BRS | L3 | 126 | ((side near wall\$1) near35 (gate)) near25 (remov\$3)) near25 (silicide) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 4 | BRS | L4 | 1161 | ((spacer\$1) near35 (gate)) near25 (remov\$3)) near25 (silicon) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |

| | Type | L # | Hits | Search Text | DBs |
|---|------|-----|------|---|--|
| 5 | BRS | L5 | 709 | 4 and silicide | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 6 | BRS | L6 | 138 | ((spacer\$1) near35 (gate)) near25 (remov\$3)) near25 (silicon) near15 (silicide) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 7 | BRS | L7 | 190 | ((silicide near15 silicon) near25 (spacer\$1)) near25 (remov\$3) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 8 | BRS | L8 | 159 | ((silicide near15 silicon) near25 (sidewall\$1)) near25 (remov\$3) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |

| | Type | L # | Hits | Search Text | DBs |
|----|------|-----|------|--|--|
| 9 | BRS | L9 | 56 | ((silicide near15 silicon) near25 (side near wall\$1)) near25 (remov\$3) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 10 | BRS | L10 | 1862 | (remov\$3) near15 (gate near dielectric) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 11 | BRS | L11 | 311 | ((remov\$3) near15 (gate near dielectric)) near25 (spacer\$1) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |
| 12 | BRS | L12 | 287 | ((remov\$3) near15 (gate near dielectric)) near25 (sidewall\$1) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |

| | Type | L # | Hits | Search Text | DBs |
|----|------|-----|------|---|--|
| 13 | BRS | L13 | 28 | ((remov\$3) near15 (gate near dielectric)) near25 (side near wall\$1) | US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B |